

Product data sheet

1. General description

Ultrafast power diode in a SOD113 (2-lead TO-220F) plastic package.

2. Features and benefits

- Fast switching
- Low forward voltage drop
- Soft recovery characteristic

3. Applications

- Discontinuous Current Mode (DCM) Power Factor Correction (PFC)
- High frequency switched-mode power supplies
- TV power supplies

4. Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V _R	reverse voltage	DC	-	-	800	V
I _{F(AV)}	average forward current	δ = 0.5; T _h ≤ 88 °C; SQW; <u>Fig. 1</u> ; Fig. 2; Fig. 3	-	-	8	A
I _{FRM}	repetitive peak forward current	δ = 0.5 ; t _p = 25 µs; T _h ≤ 88 °C; SQW	-	-	16	A
I _{FSM}	non-repetitive peak forward current	t _p = 10 ms; T _{j(init)} = 25 °C; SIN; <u>Fig. 4</u>	-	-	80	А
		t _p = 8.3 ms; T _{j(init)} = 25 °C; SIN; <u>Fig. 4</u>	-	-	88	А
Static chara	cteristics					
V _F	forward voltage	I _F = 8 A; T _j = 25 °C; <u>Fig. 6</u>	-	1.4	1.7	V
		I _F = 8 A; T _j = 150 °C; <u>Fig. 6</u>	-	1.2	1.5	V
Dynamic cha	aracteristics	·	-			
t _{rr}	reverse recovery time	$ I_F = 1 \text{ A}; \text{ V}_R = 30 \text{ V}; \text{ d}I_F/\text{d}t = 100 \text{ A}/\mu\text{s}; $	-	40	55	ns

5. Pinning information

Table 2. I	Pinning in	formation		
Pin	Symbol	Description	Simplified outline	Graphic symbol
1	К	cathode	mb	K – K – A
2	А	anode		001aaa020
mb	n.c.	mounting base; isolated	TO-220F (SOD113)	

6. Ordering information

Table 3. Ordering information							
Type number	Package						
	Name	Description	Version				
BYR29X-800P	TO-220F	plastic single-ended package; isolated heatsink mounted; 1 mounting hole; 2-lead TO-220 "full pack"	SOD113				

BYR29X-800P



7. Limiting values

Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
V _{RRM}	repetitive peak reverse voltage		-	800	V
V _{RWM}	crest working reverse voltage		-	800	V
V _R	reverse voltage	DC	-	800	V
I _{F(AV)}	average forward current	δ = 0.5 ; T _h ≤ 88 °C; SQW; <u>Fig. 1; Fig. 2</u> ; Fig. 3	-	8	A
I _{FRM}	repetitive peak forward current	δ = 0.5 ; t _p = 25 µs; T _h ≤ 88 °C; SQW	-	16	A
I _{FSM}	non-repetitive peak	t _p = 10 ms; T _{j(init)} = 25 °C; SIN; <u>Fig. 4</u>	-	80	А
	forward current	t _p = 8.3 ms; T _{j(init)} = 25 °C; SIN; <u>Fig. 4</u>	-	88	А
T _{stg}	storage temperature		-40	175	°C
Tj	junction temperature		-	175	°C

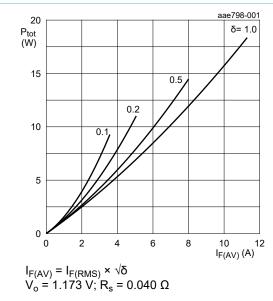
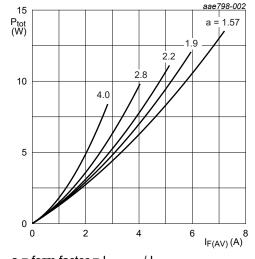


Fig. 1. Forward power dissipation as a function of average forward current; square waveform; maximum values



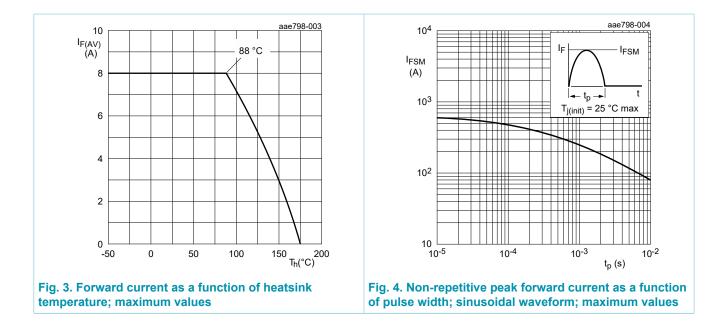
a = form factor = I $_{F(RMS)}$ / I $_{F(AV)}$ V $_{o}$ = 1.173 V; R $_{s}$ = 0.040 Ω

Fig. 2. Forward power dissipation as a function of average forward current; sinusoidal waveform; maximum values

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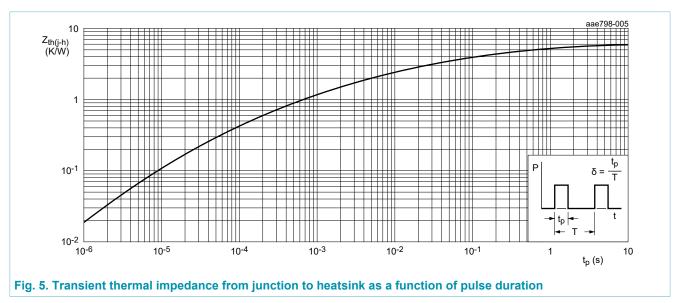
Ultrafast power diode



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8. Thermal characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
R _{th(j-h)}	thermal resistance from junction to heatsink	with heatsink compound; Fig. 5	-	-	6	K/W
R _{th(j-a)}	thermal resistance from junction to ambient free air	in free air	-	60	-	K/W



9. Isolation characteristics

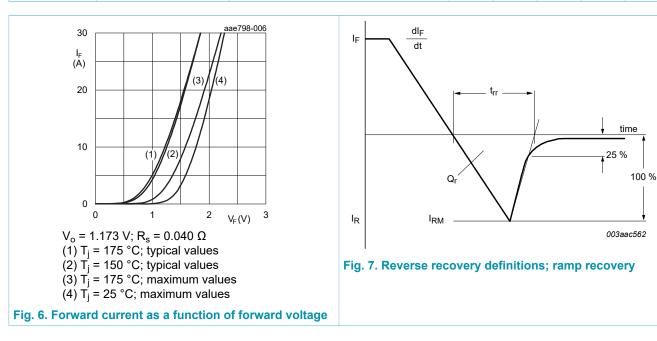
Table 6. Isolation characteristics							
Symbol	Parameter	Conditions		Min	Тур	Max	Unit
V _{isol(RMS)}	RMS isolation voltage	50 Hz \leq f \leq 60 Hz; RH \leq 65 %; from all pins to external heatsink; sinusoidal waveform; clean and dust free		-	-	2500	V
C _{isol}	isolation capacitance	from cathode to external heatsink		-	10	-	pF

10. Characteristics

Table 7. Characteristics

from cathode to external heatsink

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static chara	acteristics					
V _F	forward voltage	I _F = 8 A; T _j = 25 °C; <u>Fig. 6</u>	-	1.4	1.7	V
		I _F = 8 A; T _j = 150 °C; <u>Fig. 6</u>	-	1.2	1.5	V
I _R	reverse current	V _R = 800 V; T _j = 25 °C	-	-	10	μA
		V _R = 800 V; T _j = 150 °C	-	-	0.2	mA
Dynamic ch	haracteristics	·				
t _{rr}	reverse recovery time	$ I_F = 1 \text{ A}; V_R = 30 \text{V}; \text{d} I_F/\text{d} t = 100 \text{A}/\mu\text{s}; \\ T_j = 25 ^\circ\text{C}; \underline{\text{Fig. } 7} $	-	40	55	ns
I _{RM}	peak reverse recovery current	I_F = 1 A; V_R = 30 V; dI_F/dt = 100 A/µs; T_j = 25 °C	-	-	5	A
Qr	recovered charge	I _F = 2 A; V _R = 30 V; dI _F /dt = 20 A/s; T _i = 25 °C	-	60	110	nC





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11. Package outline

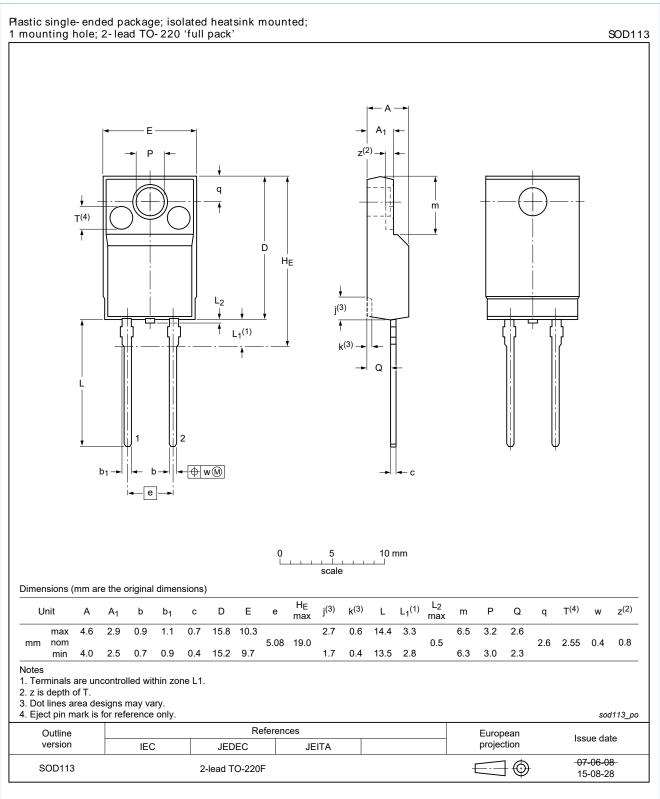


Fig. 8. Package outline TO-220F (SOD113)

BYR29X-800P

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12. Legal information

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